

AMENDMENT

Please amend the claims as follows:

1. (Currently Amended) A treatment system for the treatment of effluent gases from a semiconductor device manufacturing process, the treatment system comprising:

(a) an abatement system comprising:

- i) a burn/wet scrubber for receiving a flow of effluent gas containing a toxic constituent and for producing a flow of treated gas and a flow of waste~~[[-]]~~water containing the toxic constituent; and
- ii) a localized wastewater treatment unit comprising an ion exchange filter selected to reduce the concentration of said toxic constituent, for receiving said flow of wastewater containing the toxic constituent, [[

] (b) a local waste water treatment unit associated with the burn/wet scrubber for receiving the flow of wastewater containing the toxic constituent]] and for producing a flow of locally treated wastewater from which the toxic constituent has been abated.

2. (Currently Amended) The treatment system of claim 1 further comprising a plurality of burn/wet scrubbers in fluid communication with ~~a single local~~ said localized wastewater treatment unit.

3. (Cancelled)

4. (Cancelled)

5. (Currently Amended) The treatment system of claim 1 ~~and~~ including additionally comprising a central wastewater treatment facility for receiving and further treating the locally treated wastewater.

6. (Currently Amended) The treatment system of claim ~~[[1]]~~5 further comprising a plurality of burn/wet scrubbers and a plurality of localized wastewater treatment units wherein each said burn/wet scrubbers is in fluid communication with a ~~corresponding~~ localized wastewater treatment unit, and each said localized wastewater treatment unit is in fluid communication with the central wastewater treatment facility.

7. (Withdrawn) A method for the abatement of toxic constituents of effluent gases discharged during the manufacture of semiconductor devices, the method comprising the steps of:

- (a) oxidizing the toxic constituents of the effluent gases;
- (b) condensing the oxidized toxic constituents with water; and
- (c) abating condensed toxic constituents from water used to condense the oxidized toxic constituents.

8. (Withdrawn) The method of claim 7 wherein said step of abating the toxic constituents from the water includes providing an ion exchange filter for the filtration of toxic constituents from the water.

9. (Withdrawn) The method of claim 7 wherein the steps of oxidizing the toxic constituents and condensing the oxidized toxic constituents take place at a plurality of locations during the manufacture of the semiconductor devices.

10. (Withdrawn) The method of claim 7 and including the step of directing the water to a central wastewater treatment facility after the abatement of the toxic constituents.

11. (Withdrawn) The method of claim 7 wherein said step of abating the toxic constituents from the water includes providing a plurality of ion exchange filters for the filtration of toxic compounds from the water, before the water is directed to the central wastewater treatment facility.

12. (Withdrawn) A method of abatement of toxic constituents in the effluent from a semiconductor device manufacturing process, the method comprising:

(d) treating a flow of effluent gas containing a toxic constituent in a burn/wet scrubber to produce a flow of treated gas and a flow of wastewater containing the toxic constituent; and,

(e) locally treating the flow of wastewater containing the toxic constituent to produce a flow of locally treated wastewater from which the toxic constituent has been abated.

13. (Withdrawn) The method of claim 12 further including the step of treating the wastewater in a central wastewater treatment facility subsequent to said step of locally treating the wastewater.

14. (Withdrawn) The method of claim 12 wherein said step of locally treating the wastewater includes flowing the wastewater through an ion exchange filter.

15. (new) The treatment system of claim 1 wherein said ion exchange filter is selected to reduce the concentration of arsenic and germanium.

16. (new) The treatment system of claim 15 wherein said ion exchange filter is selected to reduce the concentration of arsenic to a concentration below 50 ppb.

17. (new) The treatment system of claim 15 wherein said ion exchange filter is selected to reduce the concentration of germanium to a concentration below 50 ppb.